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EpiGaN to Supply OMMIC with GaN/Si Material for its Newly Opened 150mm RF Power Product Line

Hasselt, Belgium, and Limeil-Brévannes Cedex, France, Oct 5th, 2017 --- *Following the inauguration of Europe's first 150mm GaN production line at OMMIC, EpiGaN and OMMIC today announced their partnership on GaN/Si epiwafers supply for RF power products aiming at future 5G wireless communication.*

EpiGaN, global supplier of GaN-on-Si and GaN-on-SiC material solutions for advanced electronic products, and OMMIC, a key provider of compound semiconductor MMICs and foundry services, are collaborating in the development of RF GaN/Si technology on 150-mm diameter wafers. They have jointly collaborated on establishing a production process based on EpiGaN's differentiating GaN/Si material technology with in-situ grown SiN passivation. They will cooperate directly to move this technology to 150-mm diameter wafers, targeting future 5G wireless communication standards, for which OMMIC last week announced a large project with a 5G equipment supplier.

The advent of the 5G era is going to revolutionize long-distance communications. To provide users with exceptionally high-speed wireless connections, ultra-low latency and enhanced mobile broadband, a new semiconductor technology – GaN – is required in applications such as multimedia streaming, autonomous driving, machine-to-machine communication with billions of interconnected sensors or Internet-of-Things, to transmit and receive RF signals in the utmost efficient way.

"EpiGaN is honored to team up with OMMIC for scaling up to a 150-mm GaN/Si process line based on EpiGaN's differentiating technology addressing products for 5G," commented EpiGaN CEO Dr Marianne Germain. "We offer many attractive USPs for RF power, which add value to device designers, such as in-situ SiN passivation for enhanced device robustness, or very low RF losses up to 100GHz. We are proud of the high-frequency capability of our material, which enables a very cost-efficient and energy-efficient GaN technology for the higher frequency bands targeted by 5G."

"The next-generation 5G standard will require GaN as an enabling semiconductor technology to provide a step-up in performance," stated OMMIC CEO Dr Marc Rocchi. "Only then will the experience for the end user be superb. Teaming up with EpiGaN is an essential element of our growth strategy and it enables us to meet the required volume and quality levels for our 5G GaN MMICs."

About EpiGaN

EpiGaN provides industry-leading III-nitride epitaxial material solutions for top-performance devices, offering early access to a unique and proven GaN/Si and GaN/SiC technology for next-generation power switching, RF power and advanced sensor solutions. EpiGaN is a VC-backed company, incorporated in 2010 as a spin-off of imec. EpiGaN has the ISO 9001:2015 certification for the design and manufacturing of GaN epiwafers for electronics. EpiGaN is using its well recognized strong expertise in GaN technology to manufacture GaN material at their production site in Hasselt, Belgium, supporting its customers with access to a unique and robust technology.

EpiGaN's HVRF power structures are available on both SiC (up to 150mm) and Si substrates (up to 200mm). They offer high power densities for mm-wave bands combined with lowest RF losses (<0.5dB/mm up to 50GHz, <1dB/mm up to 100 GHz). An additional competitive advantage of EpiGaN's wafer technology is the in-situ SiN capping layer. This provides superior surface passivation and the use of pure, ultra-thin AlN layers as barrier materials results in superior mmW performance, reducing short-channel transistor effects.

Key applications of EpiGaN materials are in power supplies for consumer electronics, AC drives, UPS systems, hybrid electric vehicles, solar inverters, smart-grid applications, 4/5G RF wireless communication systems, IoT and sensors. www.epigan.com

About OMMIC

OMMIC is an independent company doing microwave and millimeter wave research, development and manufacturing of III-V products for telecommunication, instrumentation, fiber optic, satellite and defense applications. Headquartered in Limeil-Brévannes, France, OMMIC was founded in 2000 as a spinout from Philips Microwave Limeil (PML). OMMIC is a supplier of MMIC circuits, Foundry services and of Eepitaxial wafers based on III-V (GaAs, GaN and InP) materials. As a leader in advanced technologies, OMMIC provides its customers with cutting edge performance for Telecommunication, Space and Defence Applications. The design and manufacturing facilities of OMMIC are based near Paris, France. The State of the Art Technologies include mixed mode E/D PHEMT, Low Noise and Power PHEMT, Metamorphic HEMT and InP DHBT allowing the design of a wide range of MMICs including LNAs from 900 MHz to 160 GHz, Highly Integrated T/R Functions and Millimeter wave Power Amplifiers.
OMMIC offers standard products as well as custom designs. OMMIC has a long history of providing Foundry Services with complete design kits, training and design assistance. Hermetic and plastic packaging, test and qualification (including space and military) are also available.

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